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The invention relates to the semiconductor production.

The process for obtaining semiconductor nanostructural zones includes deposition on one of the semiconductor crystal surfaces of a mask with an open portion, electrochemical pickling at anodizing in an aqueous NaCl solution and removal of mask.

The result of the invention consists in obtaining semiconductor nanostructural zones with the morphology adjusted by the concentration of the NaCl solution and by the applied electrical parameters, using the NaCl solution which does not present hazard for personnel health or for the environment.

Claims: 1
Fig.: 4